

November 2014

FDBL0065N40

N-Channel PowerTrench[®] MOSFET 40 V, 300 A, 0.65 m Ω

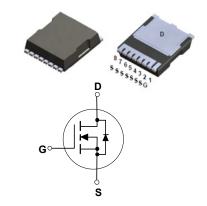
Features

- Typical $R_{DS(on)}$ = 0.5 m Ω at V_{GS} = 10V, I_D = 80 A
- Typical $Q_{q(tot)}$ = 220 nC at V_{GS} = 10V, I_D = 80 A
- UIS Capability
- RoHS Compliant

Applications

- Industrial Motor Drive
- Industrial Power Supply
- Industrial Automation
- Battery Operated tools
- Battery Protection
- Solar Inverters
- UPS and Energy Inverters
- Energy Storage
- Load Switch





For current package drawing, please refer to the Fairchild website at https://www.fairchildsemi.com/evaluate/package-specifications/packageDetails.html?id=PN_PSOFA-008

MOSFET Maximum Ratings T_J = 25°C unless otherwise noted.

Symbol	Parameter		Ratings	Units
V_{DSS}	Drain-to-Source Voltage		40	V
V_{GS}	Gate-to-Source Voltage		±20	V
1	Drain Current - Continuous (V _{GS} =10) (Note 1)	$T_C = 25^{\circ}C$	300	A
'D	Pulsed Drain Current	T _C = 25°C	See Figure 4	A
E _{AS}	Single Pulse Avalanche Energy	(Note 2)	1064	mJ
D	Power Dissipation		429	W
P_{D}	Derate Above 25°C		2.86	W/°C
T _J , T _{STG}	Operating and Storage Temperature		-55 to + 175	°C
$R_{\theta JC}$	Thermal Resistance, Junction to Case		0.35	°C/W
$R_{\theta JA}$	Maximum Thermal Resistance, Junction to Ambient	(Note 3)	43	°C/W

Notes:

- 1: Current is limited by bondwire configuration.
- 2: Starting $T_J = 25^{\circ}C$, L = 0.3mH, $I_{AS} = 84$ A, $V_{DD} = 40$ V during inductor charging and $V_{DD} = 0$ V during time in avalanche.
- 3: R_{0,JA} is the sum of the junction-to-case and case-to-ambient thermal resistance, where the case thermal reference is defined as the solder mounting surface of the drain pins. R_{0,JC} is guaranteed by design, while R_{0,JA} is determined by the board design. The maximum rating presented here is based on mounting on a 1 in² pad of 2oz copper.

Package Marking and Ordering Information

Device Marking	Device	Package			
FDBL0065N40	FDBL0065N40	MO-299A	-	-	-

Units

Max.

Electrical Characteristics $T_J = 25$ °C unless otherwise noted.

Parameter

Off Ch	Off Characteristics							
B _{VDSS}	Drain-to-Source Breakdown Voltage	$I_D = 250 \mu A$,	V _{GS} = 0V	40	-	-	V	
1	Drain-to-Source Leakage Current	V _{DS} =40V,	$T_J = 25^{\circ}C$	-	-	1	μΑ	
IDSS	Dialii-to-Source Leakage Current	$V_{GS} = 0V$	$T_J = 175^{\circ}C \text{ (Note 4)}$	-	-	1	mA	
I_{GSS}	Gate-to-Source Leakage Current	$V_{GS} = \pm 20V$		1	-	±100	nA	

Test Conditions

Min.

Тур.

On Characteristics

Symbol

$V_{GS(th)}$	Gate to Source Threshold Voltage	$V_{GS} = V_{DS}, I_D = 250 \mu A$		2.0	3.0	4.0	V
D	no. I I rain to Source (In Registance	I _D = 80A,	$T_J = 25^{\circ}C$	-	0.50	0.65	mΩ
NDS(on)		V _{GS} = 10V	$T_J = 175^{\circ}C \text{ (Note 4)}$	-	0.86	1.10	mΩ

Dynamic Characteristics

C _{iss}	Input Capacitance	2514.14		-	15900	-	pF
C _{oss}	Output Capacitance	$V_{DS} = 25V, V_{GS} = 100$	$V_{DS} = 25V, V_{GS} = 0V,$ - f = 1MHz		4025	-	pF
C _{rss}	Reverse Transfer Capacitance	1 - 11VII 12			604	-	pF
R_g	Gate Resistance	f = 1MHz		-	2.6	-	Ω
$Q_{g(ToT)}$	Total Gate Charge at 10V	$V_{GS} = 0$ to 10V	V _{DD} = 20V	-	220	296	nC
$Q_{g(th)}$	Threshold Gate Charge	$V_{GS} = 0 \text{ to } 2V$	I _D = 80A	-	29	39	nC
Q_{gs}	Gate to Source Gate Charge		_	-	73	-	nC
Q_{gd}	Gate to Drain "Miller" Charge			-	41	-	nC

Switching Characteristics

t _{on}	Turn-On Time		-	-	221	ns
t _{d(on)}	Turn-On Delay		-	54	1	ns
t _r	Rise Time	V _{DD} = 20V, I _D = 80A,	-	82	-	ns
t _{d(off)}	Turn-Off Delay	V_{GS} = 10V, R_{GEN} = 6Ω	-	106	-	ns
t _f	Fall Time		-	52	-	ns
t _{off}	Turn-Off Time		-	-	215	ns

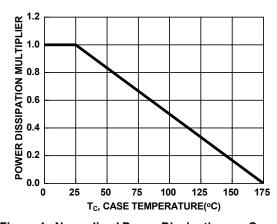
Drain-Source Diode Characteristics

V	Source to Drain Diode Voltage	I_{SD} =80A, V_{GS} = 0V	0A, V _{GS} = 0V	-	1.25	V
V_{SD}	Source to Drain Diode Voltage	I_{SD} = 40A, V_{GS} = 0V	-	-	1.2	V
t _{rr}	Reverse Recovery Time	$I_F = 80A$, $dI_{SD}/dt = 100A/\mu s$,	-	119	133	ns
Q _{rr}	Reverse Recovery Charge	V _{DD} =32V	-	228	274	nC

Note:

4: The maximum value is specified by design at T_J = 175°C. Product is not tested to this condition in production.

Typical Characteristics



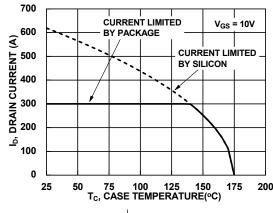


Figure 1. Normalized Power Dissipation vs. Case Temperature

Figure 2. Maximum Continuous Drain Current vs. Case Temperature

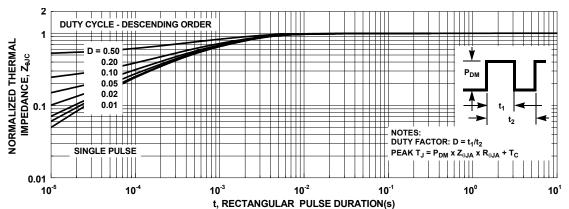


Figure 3. Normalized Maximum Transient Thermal Impedance

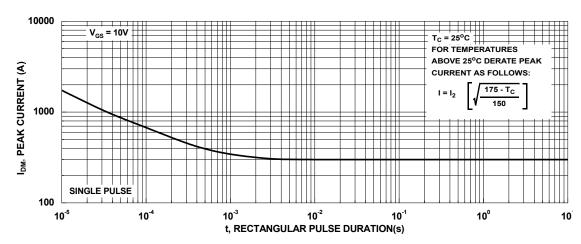


Figure 4. Peak Current Capability

Typical Characteristics

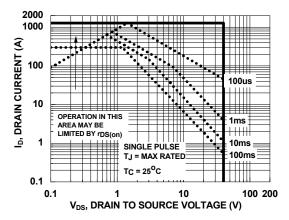
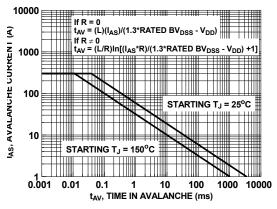


Figure 5. Forward Bias Safe Operating Area



NOTE: Refer to Fairchild Application Notes AN7514 and AN7515

Figure 6. Unclamped Inductive Switching

Capability

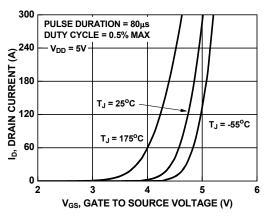


Figure 7. Transfer Characteristics

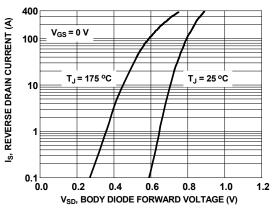


Figure 8. Forward Diode Characteristics

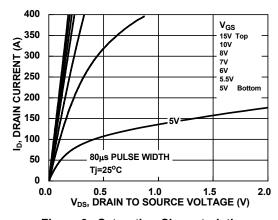


Figure 9. Saturation Characteristics

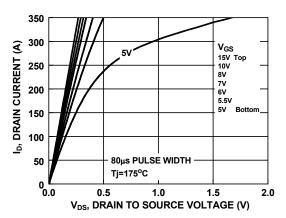


Figure 10. Saturation Characteristics

Typical Characteristics

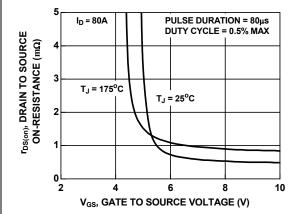


Figure 11. R_{DSON} vs. Gate Voltage

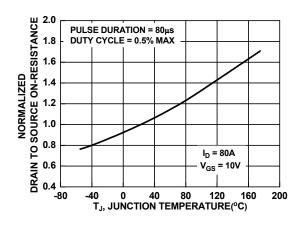


Figure 12. Normalized R_{DSON} vs. Junction Temperature

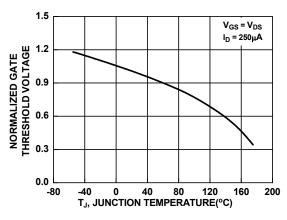


Figure 13. Normalized Gate Threshold Voltage vs. Temperature

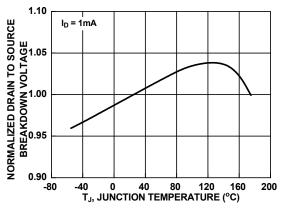


Figure 14. Normalized Drain to Source Breakdown Voltage vs. Junction Temperature

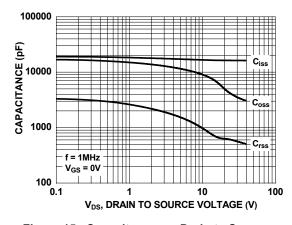


Figure 15. Capacitance vs. Drain to Source Voltage

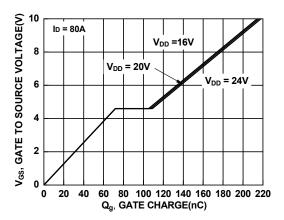


Figure 16. Gate Charge vs. Gate to Source Voltage





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